
PART NUMBER

54F32B2A-ROCS

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer. (OCM)

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
 - Class Q Military
 - Class V Space Level

Qualified Suppliers List of Distributors (QSLD)

- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

54F/74F32

Quad 2-Input OR Gate

General Description

This device contains four independent gates, each of which performs the logic OR function.

Features

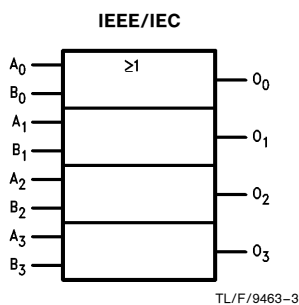
- Guaranteed 4000V minimum ESD protection

Commercial	Military	Package Number	Package Description
74F32PC		N14A	14-Lead (0.300" Wide) Molded Dual-In-Line
	54F32DM (Note 2)	J14A	14-Lead Ceramic Dual-In-Line
74F32SC (Note 1)		M14A	14-Lead (0.150" Wide) Molded Small Outline, JEDEC
74F32SJ (Note 1)		M14D	14-Lead (0.300" Wide) Molded Small Outline, EIAJ
	54F32FM (Note 2)	W14B	14-Lead Cerpack
	54F32LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

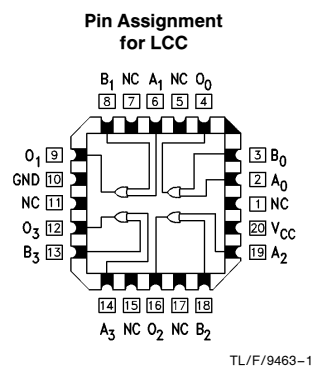
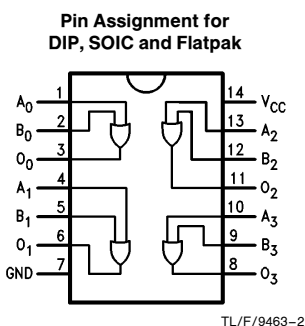
Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMOB, FMOB and LMOB.

Logic Symbol



Connection Diagrams



Unit Loading/Fan Out

Pin Names	Description	54F/74F	
		U.L. HIGH/LOW	Input I_{IH}/I_{IL} Output I_{OH}/I_{OL}
A_n, B_n O_n	Inputs Outputs	1.0/1.0 50/33.3	20 μ A/ - 0.6 mA - 1 mA/20 mA

TRI-STATE® is a registered trademark of National Semiconductor Corporation.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	−65°C to +150°C
Ambient Temperature under Bias	−55°C to +125°C
Junction Temperature under Bias	−55°C to +175°C
Plastic	−55°C to +150°C

V_{CC} Pin Potential to Ground Pin −0.5V to +7.0V

Input Voltage (Note 2) −0.5V to +7.0V

Input Current (Note 2) −30 mA to +5.0 mA

Voltage Applied to Output in HIGH State (with V_{CC} = 0V)
Standard Output −0.5V to V_{CC}
TRI-STATE® Output −0.5V to +5.5V

Current Applied to Output in LOW State (Max) twice the rated I_{OL} (mA)

ESD Last Passing Voltage (Min) 4000V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature	
Military	−55°C to +125°C
Commercial	0°C to +70°C
Supply Voltage	
Military	+4.5V to +5.5V
Commercial	+4.5V to +5.5V

DC Electrical Characteristics

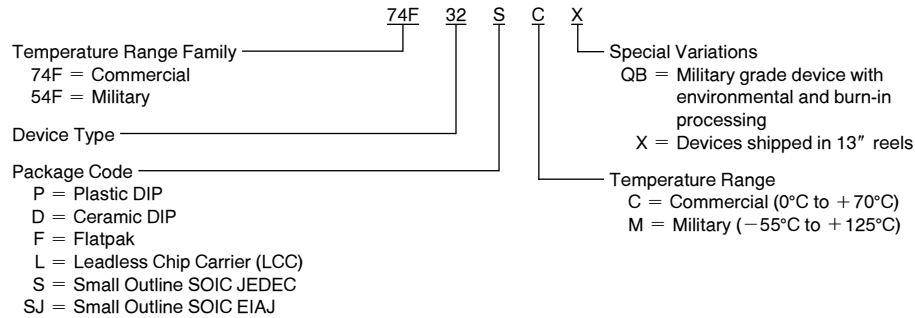
Symbol	Parameter	54F/74F			Units	V _{CC}	Conditions
		Min	Typ	Max			
V _{IH}	Input HIGH Voltage	2.0			V		Recognized as a HIGH Signal
V _{IL}	Input LOW Voltage			0.8	V		Recognized as a LOW Signal
V _{CD}	Input Clamp Diode Voltage			−1.2	V	Min	I _{IN} = −18 mA
V _{OH}	Output HIGH Voltage	54F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC}	2.5 2.5 2.7		V	Min	I _{OH} = −1 mA I _{OH} = −1 mA I _{OH} = −1 mA
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}		0.5 0.5	V	Min	I _{OL} = 20 mA I _{OL} = 20 mA
I _{IH}	Input HIGH Current	54F 74F		20.0 5.0	μA	Max	V _{IN} = 2.7V
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F		100 7.0	μA	Max	V _{IN} = 7.0V
I _{CEX}	Output HIGH Leakage Current	54F 74F		250 50	μA	Max	V _{OUT} = V _{CC}
V _{ID}	Input Leakage Test	74F	4.75		V	0.0	I _{ID} = 1.9 μA All Other Pins Grounded
I _{OD}	Output Leakage Circuit Current	74F		3.75	μA	0.0	V _{IOD} = 150 mV All Other Pins Grounded
I _{IL}	Input LOW Current			−0.6	mA	Max	V _{IN} = 0.5V
I _{OS}	Output Short-Circuit Current		−60	−150	mA	Max	V _{OUT} = 0V
I _{CCH}	Power Supply Current		6.1	9.2	mA	Max	V _O = HIGH
I _{CCL}	Power Supply Current		10.3	15.5	mA	Max	V _O = LOW

AC Electrical Characteristics

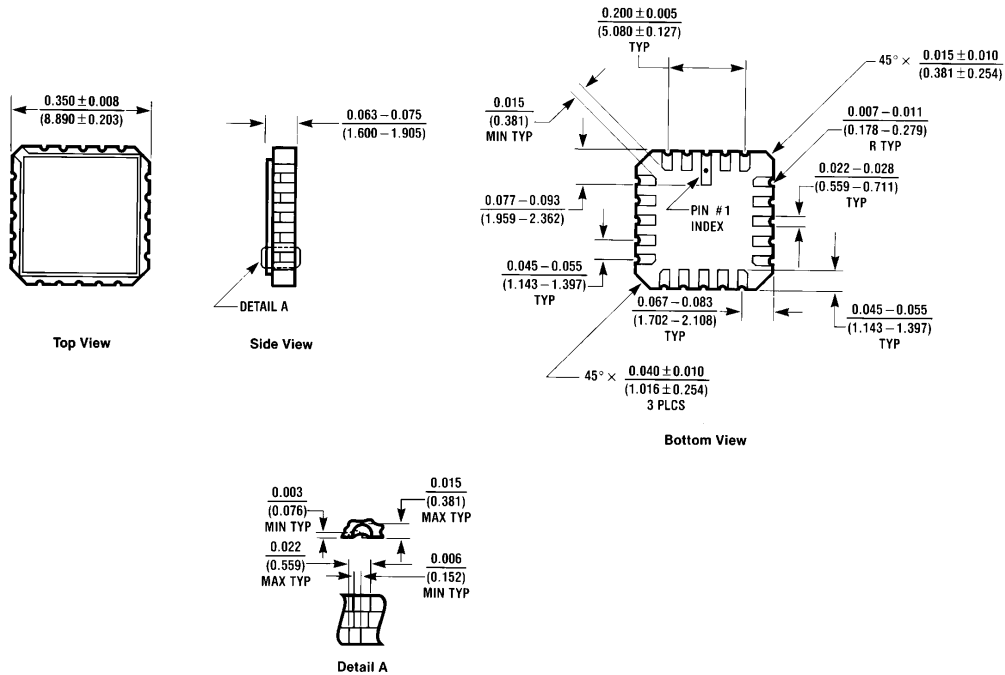
Symbol	Parameter	74F			54F		74F		Units
		T _A = +25°C V _{CC} = +5.0V C _L = 50 pF			T _A , V _{CC} = Mil C _L = 50 pF		T _A , V _{CC} = Com C _L = 50 pF		
		Min	Typ	Max	Min	Max	Min	Max	
t _{PLH}	Propagation Delay	3.0	4.2	5.6	3.0	7.5	3.0	6.6	ns
t _{PHL}	A _n , B _n to O _n	3.0	4.0	5.3	2.5	7.5	3.0	6.3	

Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:



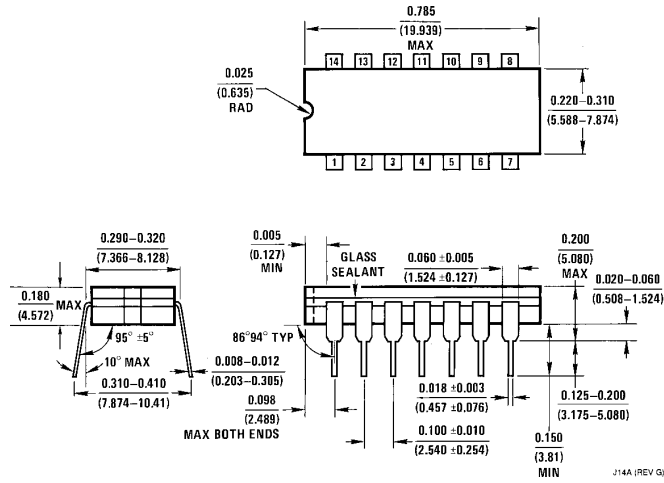
Physical Dimensions inches (millimeters)



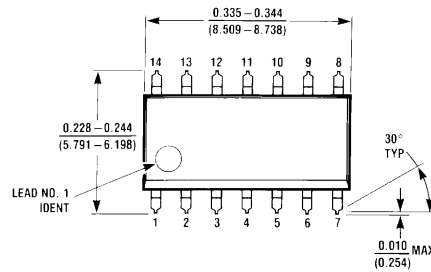
20-Lead Ceramic Leadless Chip Carrier (L)
NS Package Number E20A

E20A (REV D)

Physical Dimensions inches (millimeters) (Continued)

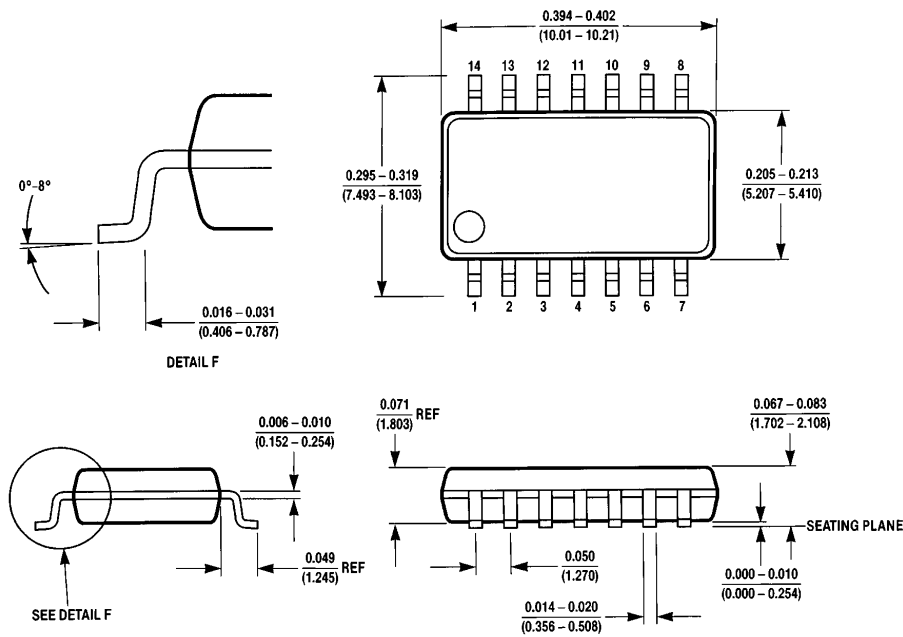


14-Lead Ceramic Dual-In-Line Package (D)
NS Package Number J14A



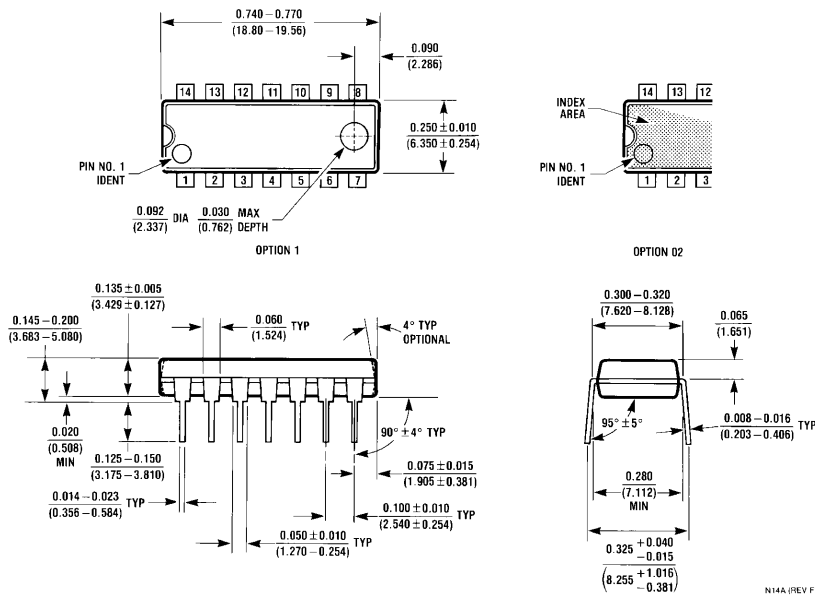
14-Lead (0.150" Wide) Molded Small Outline Package, JEDEC (S)
NS Package Number M14A

Physical Dimensions inches (millimeters) (Continued)



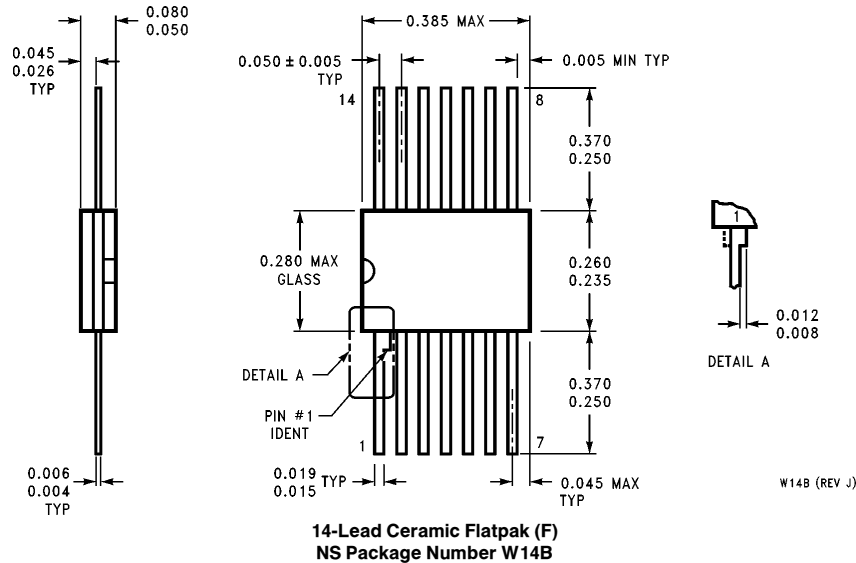
M14D (REV A)

**14-Lead (0.300" Wide) Molded Small Outline Package, EIAJ (SJ)
NS Package Number M14D**



N14A (REV F)

**14-Lead (0.300" Wide) Molded Dual-In-Line Package (P)
NS Package Number N14A**

Physical Dimensions inches (millimeters) (Continued)**LIFE SUPPORT POLICY**

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